

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of  
H. Fujimura et al.

Docket: 2060.4

Serial No. :

Filed:

For: DIAMOND-COATED SILICON AND MANUFACTURING METHOD THEREOF

**PRELIMINARY AMENDMENT**

Mail Stop PCT  
Commissioner for Patents  
P. O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

Preliminary to the examination of the above-identified application, please amend the application as follows:

**In the Claims:**

Please amend claims as follows:

1. (original) A diamond-coated silicon comprising a silicon substrate having a thickness of 500  $\mu\text{m}$  or less coated at least partially with electrically conductive diamond, wherein the silicon substrate is manufactured by the plate-like crystal growth process.

2. (original) The diamond-coated silicon according to claim 1, wherein the plate-like crystal growth process is at least one selected from the EFG process, the string ribbon process and the dendritic web process.